

DEC 29 2003

Application No.: 10/015,414

Docket No.: JCLA7737

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of :
Application No. : 10/015,414
Filed : December 12, 2001
For : Method For Programming And Erasing Non-Volatile Memory With
Nitride Tunneling Layer
Applicant : Tso-Hung Fan
Examiner : Pham, Ly D
Art Unit : 2818

PRELIMINARY AMENDMENT

Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

The Advisory Office Action mailed December 8, 2003 has been carefully considered. In response thereto, please enter the following amendments for RCE and consider the following remarks.